

Vishay Siliconix

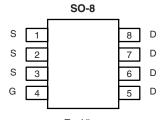
N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
12	0.003 at V _{GS} = 4.5 V	25		
	0.004 at V _{GS} = 2.5 V	20		

FEATURES

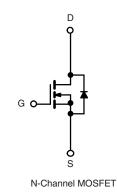
- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFETs: 2.5 V Rated
- 100 % R_g Tested





Top View





ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	12		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	– I _D	25	17	•	
	T _A = 70 °C		20	13		
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	60		A	
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.3		
	T _A = 25 °C	P _D	3.5	1.6	w	
Maximum Power Dissipation ^a	T _A = 70 °C	' D	2.2	1	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	R _{thJA}	29	35	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	67	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted Parameter Symbol Test Conditions				Тур.	Max.	Unit	
Parameter Symbol Test Conditions Min. Typ. Max. Unit Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.6			V	
Gate-Body Leakage	I _{GSS}				± 100	nA	
	I _{DSS}	$V_{DS} = 9.6 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		V_{DS} = 9.6 V, V_{GS} = 0 V, T_{J} = 55 °C			5	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$				Α	
Drain-Source On-State Resistance ^a	Б	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 25 \text{ A}$		0.0024	0.003	Ω	
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0031	0.004		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 6 V, I_{D} = 25 A$		80		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = 2.9 A, $V_{\rm GS}$ = 0 V		0.75	1.1	V	
Dynamic ^b	•		•	•			
Total Gate Charge	Qg			40	60	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = 6 V, V_{GS} = 4.5 V, I_{D} = 25 A		6.7			
Gate-Drain Charge	Q _{gd}			9.2			
Gate Resistance	Rg		1.0	1.7	2.9	Ω	
Turn-On Delay Time	t _{d(on)}			40	60		
Rise Time	t _r	V_{DD} = 6 V, R_L = 6 Ω		40	60]	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{1}$ A, V_GEN = 4.5 V, R_g = 6 Ω		140	210	ns	
Fall Time	t _f			70	100		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs		50	80		

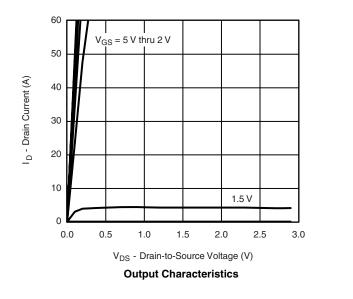
Notes:

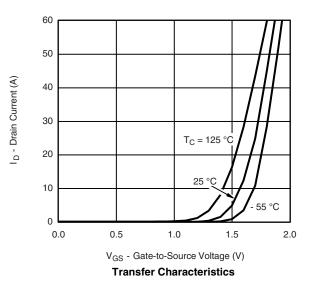
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

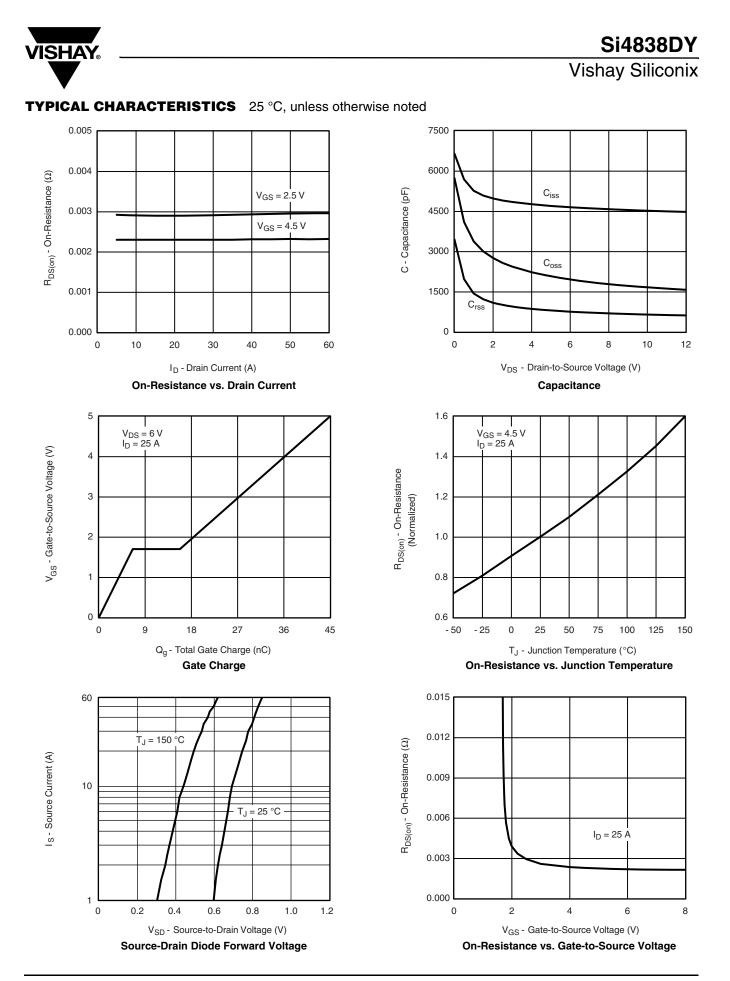
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





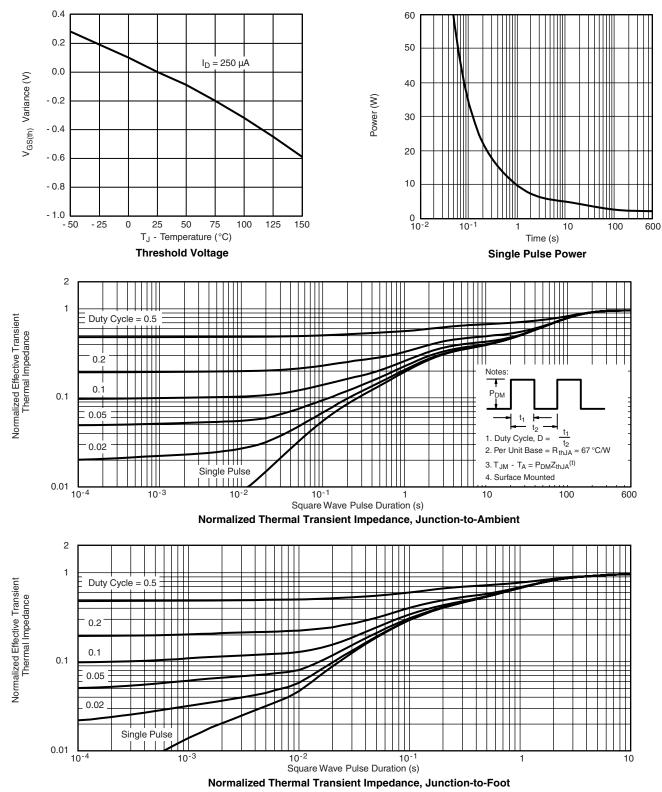


Document Number: 71359 S09-0221-Rev. D, 09-Feb-09

Si4838DY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71359.





Package Information

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	INCHES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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